

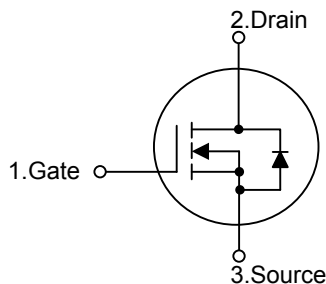
**4N80****Power MOSFET****4.0A, 800V N-CHANNEL
POWER MOSFET****DESCRIPTION**

The UTC **4N80** is a N-channel mode power MOSFET using UTC's advanced technology to provide customers planar stripe and DMOS technology. This technology is specialized in allowing a minimum on-state resistance, and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **4N80** is universally applied in high efficiency switch mode power supply.

FEATURES

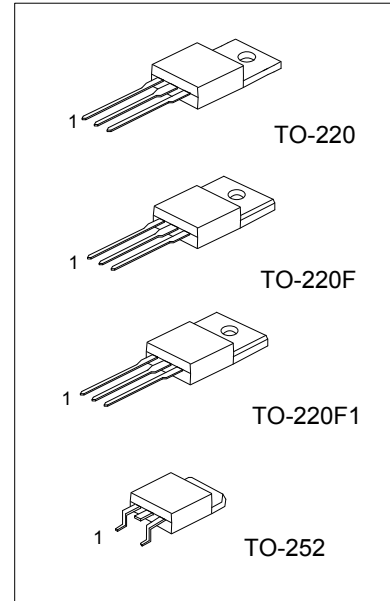
- * $R_{DS(on)}=3.0\Omega$ @ $V_{GS}=10V$
- * High switching speed
- * Improved dv/dt capability
- * 100% avalanche tested

SYMBOL**ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
4N80L-TA3-T	4N80G-TA3-T	TO-220	G	D	S	Tube
4N80L-TF3-T	4N80G-TF3-T	TO-220F	G	D	S	Tube
4N80L-TF1-T	4N80G-TF1-T	TO-220F1	G	D	S	Tube
4N80L-TN3-R	4N80G-TN3-R	TO-252	G	D	S	Tape Reel
4N80L-TN3-T	4N80G-TN3-T	TO-252	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

4N80L - TA3 - T	(1) Packing Type (2) Package Type (3) Lead Free	(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1 TN3: TO-252 (3) G: Halogen Free, L: Lead Free
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■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	800	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	4.0	A
	Pulsed (Note 2)	I_{DM}	16	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	460	mJ
	Repetitive (Note 2)	E_{AR}	13	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.0	V/ns
Power Dissipation	TO-220	P_D	106	W
	TO-220F/TO-220F1		36	W
	TO-252		50	W
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55~+150	$^{\circ}\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L=57\text{mH}$, $I_{AS}=4\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J=25^{\circ}\text{C}$

4. $I_{SD} \leq 4\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J=25^{\circ}\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220	θ_{JA}	62.5	$^{\circ}\text{C}/\text{W}$
	TO-220F/TO-220F1		62.5	$^{\circ}\text{C}/\text{W}$
	TO-252		110	$^{\circ}\text{C}/\text{W}$
Junction to Case	TO-220	θ_{JC}	1.18	$^{\circ}\text{C}/\text{W}$
	TO-220F/TO-220F1		3.47	$^{\circ}\text{C}/\text{W}$
	TO-252		2.5	$^{\circ}\text{C}/\text{W}$

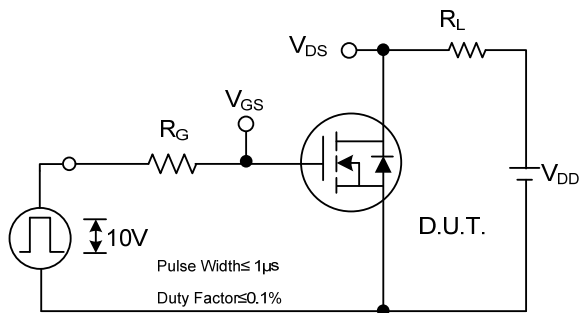
■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250μA	800			V
Breakdown Voltage Temperature Coefficient		ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		950		mV/°C
Drain-Source Leakage Current		I _{DSS}	V _{DS} =800V, V _{GS} =0V			10	μA
			V _{DS} =640V, T _C =125°C			100	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{DS} =0V , V _{GS} =30V			100	nA
	Reverse		V _{DS} =0V , V _{GS} =-30V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	3.0		5.0	V
Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =2A		2.3	3.0	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		680	880	pF
Output Capacitance		C _{OSS}			75	100	pF
Reverse Transfer Capacitance		C _{RSS}			8.6	12	pF
SWITCHING PARAMETERS							
Total Gate Charge		Q _G	V _{DS} =640V, V _{GS} =10V, I _D =4A (Note 1,2)		19	25	nC
Gate-Source Charge		Q _{GS}			4.2		nC
Gate-Drain Charge		Q _{GD}			9.1		nC
Turn-ON Delay Time		t _{D(ON)}	V _{DD} =400V, I _D =4A, R _G =25Ω (Note 1,2)		16	40	ns
Turn-ON Rise Time		t _R			45	100	ns
Turn-OFF Delay Time		t _{D(OFF)}			35	80	ns
Turn-OFF Fall Time		t _F			35	80	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				4	A
Maximum Body-Diode Pulsed Current		I _{SM}				16	A
Drain-Source Diode Forward Voltage		V _{SD}	I _S =4A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time		t _{rr}	V _{GS} =0V, I _S =4A,		575		ns
Body Diode Reverse Recovery Charge		Q _{RR}	dl _F /dt=100A/μs (Note 1)		3.65		μC

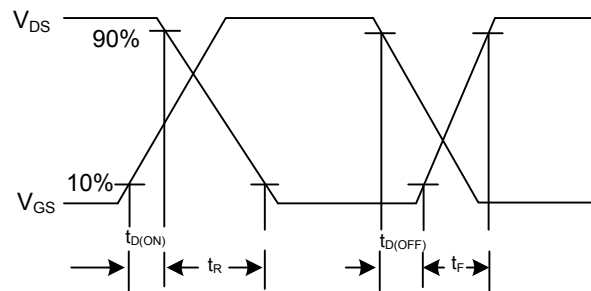
Note: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%

2. Essentially independent of operating temperature

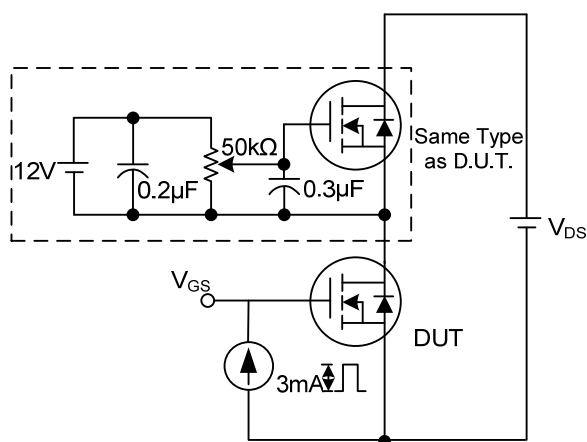
■ TEST CIRCUITS AND WAVEFORMS(Cont.)



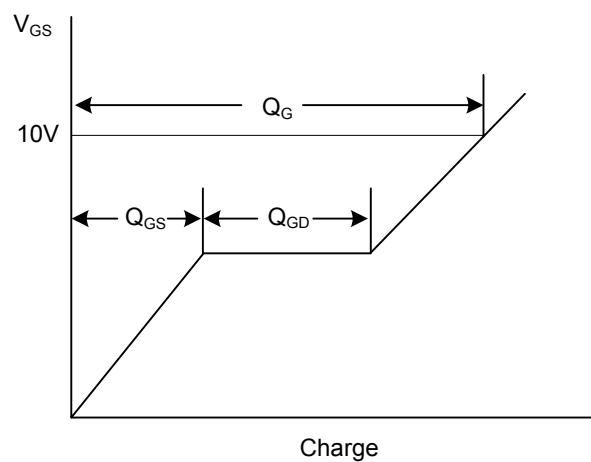
Switching Test Circuit



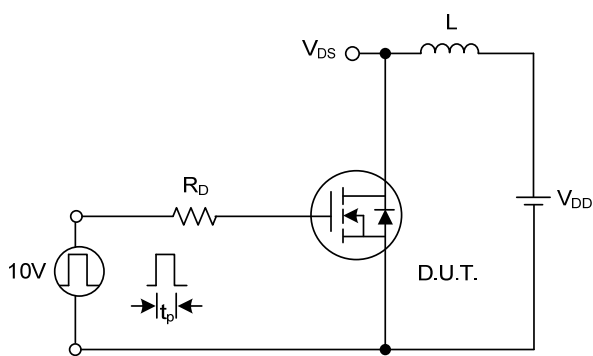
Switching Waveforms



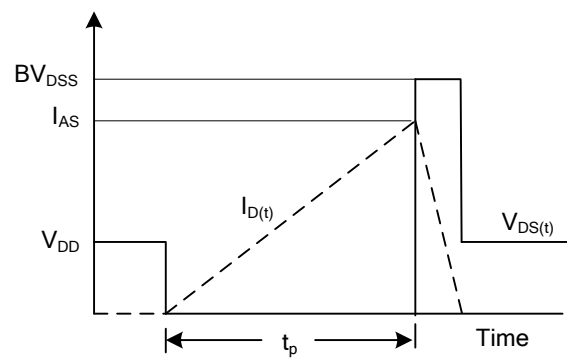
Gate Charge Test Circuit



Gate Charge Waveform

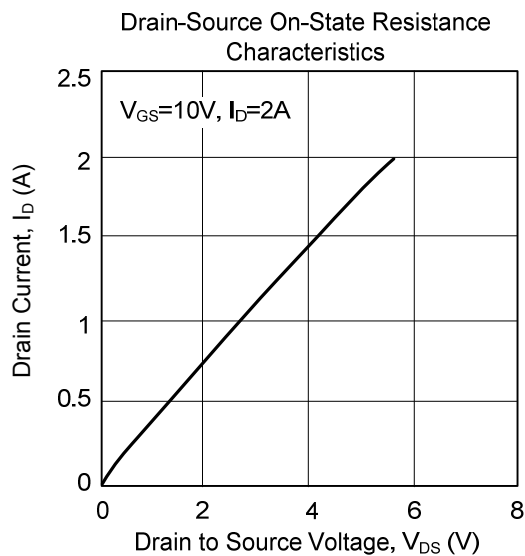
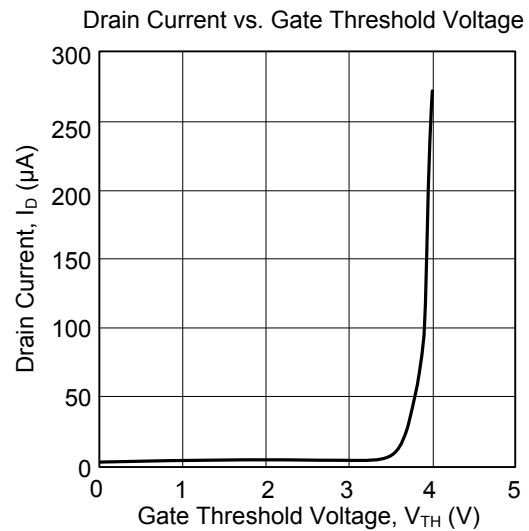
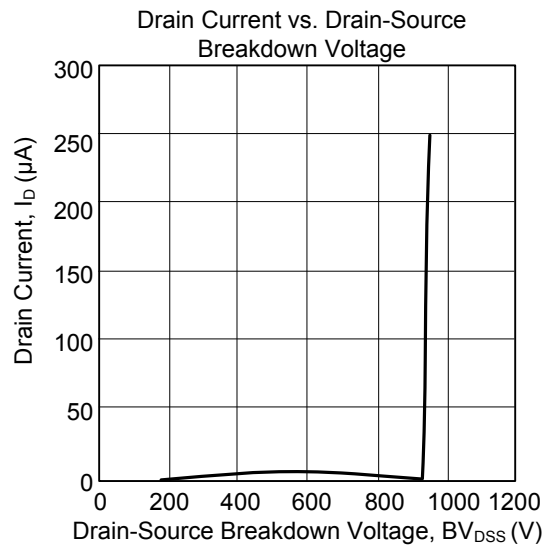


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



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